



## T-Series IGBT Modules – Standard-Type

The new Mitsubishi Electric 7<sup>th</sup> Generation Standard-Type IGBTs for 650V, 1200V and 1700V have been developed for the purpose of highest power density inverters and best-in-class thermal behavior.

The new 7<sup>th</sup> Generation CSTBT™ and diode chip set provides high efficiency by reducing both dynamic and static losses. The innovative TMS packaging technology provides very low thermal impedance, low package inductance and high thermal cycling capacity. The new Mitsubishi Standard-Type modules facilitate a high performance and reliability and compact inverter design.

The well established 34mm and 62mm package styles greatly simplify the design of medium power inverters for various applications like industrial drives, wind power, solar power and UPS. The newly introduced 48mm package for 300A and 400A rated currents enables a more compact inverter size than with comparable modules in 62mm outline.

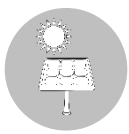
The 62mm package is a defacto standard in the market since many years. The 7th Generation extends the rated current range of this 62mm standard package, pushing its limits from previously 450A/1200V to 600A/1200V. This gives advantages in terms of operational inverter power, efficiency, reliability and even switching frequency.

Product Advantages	User benefits	Achieved by
<ul style="list-style-type: none"> <li>❑ Low-loss 7<sup>th</sup> generation CSTBT™</li> <li>❑ Low package inductance</li> <li>❑ Low internal electrical resistance</li> <li>❑ High thermal conductivity</li> <li>❑ Compact size</li> <li>❑ Highest power density</li> <li>❑ Wide power range</li> <li>❑ Light weight</li> </ul>	Extended module life time	<ul style="list-style-type: none"> <li>• High thermal cycling capability by new TMS-Technology</li> <li>• Extended power cycle life-time by <math>\Delta T_j</math> swing reduction with lowest <math>R_{th(j-c)}</math></li> </ul>
	Reduction of assembly costs	<ul style="list-style-type: none"> <li>• production lot-independent paralleling capability</li> </ul>
	High power density	<ul style="list-style-type: none"> <li>• Low loss 7th gen. Chipset</li> <li>• Lowest thermal resistance <math>R_{th(j-c)}</math> by TMS-Technology</li> </ul>
	Scalability of power classes	<ul style="list-style-type: none"> <li>• full power rating line-up of 650V, 1200V and 1700V modules</li> </ul>

Circuit	Topology	Package outline	Package size	650V	1200V	1700V
2in1 IGBT	D 		34mm x 94mm	100A	100A	75A
			150A	150A	100A	
			48mm x 94mm	300A	200A	150A
			400A	300A	200A	
2in1 AC switch	C1 		62mm x 108mm		450A	300A
			600A	600A	400A	
2in1 Diode	D 		62mm x 108mm		450A	
					600A	800A



Industrial



Solar



Wind



Power  
Transmission

### TMS (Thick-Metal-Substrate)-Technology

The newly introduced TMS-Technology is a packaging technology developed for realizing low inductance and very high thermal conductivity. Instead of the conventional package structure with several ceramic substrates soldered to a copper baseplate, the Thick-Metal-Substrate contains a high thermal conductive **silicon nitride ceramic** with thick copper layers brazed directly to the top and bottom sides.

The **thick copper layer** underneath the IGBT chip provides low lead resistance and thus allows a higher current density. At the same time, it enables a better heat spreading directly next to the chip. This, in combination with the elimination of the substrate solder, means that both the thermal resistance and temperature cycling capacity are improved.

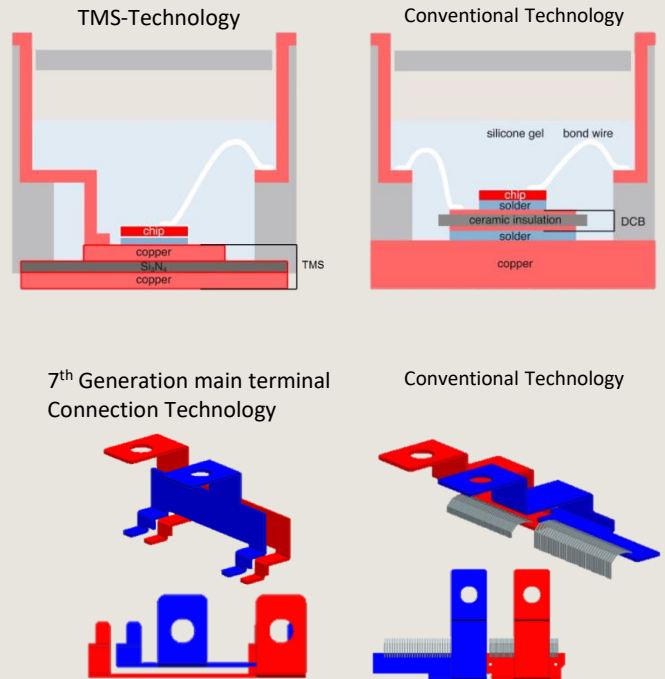
The **symmetrically stacked structure** of the TMS- Technology prevents the typical bending of baseplates in operation. This improves the thermal interface between the module and the heatsink.

Finally the total thermal resistance from junction to heatsink is reduced by more than half compared to conventional modules.

The TMS contains **one common substrate** instead of multi substrate arrangements as used in conventional modules. This expands the effective mounting area for chips and by eliminating wire bond interconnections - the internal stray inductance and lead resistance are reduced.

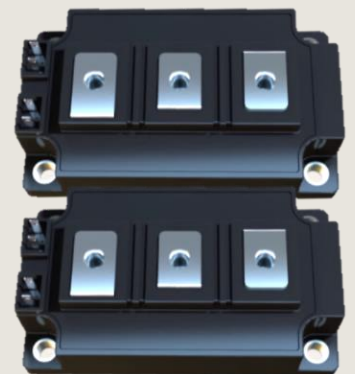
The main terminals are connected to the TMS by laminated internal bus bar with **increased laminated area** and **ultrasonic bonding**. This reduces the package inductance by 30% and contributes to low lead resistance .

*new*



### User friendly scalability by paralleling

The Standard-Type of 7<sup>th</sup> Generation IGBT Moduls is also available with an parallel specification. Using this specification the  $V_{CEsat}$  value is controlled and users can easily apply parallel connection without module selection, ranking or considering lot codes during production or processes.



**Mitsubishi Electric Europe B.V. (European Headquarters)**

– Semiconductor European Business Group –

Mitsubishi-Electric-Platz 1 / D-40882 Ratingen

Phone +49 (0) 2102 486 0

Fax +49 (0) 2102 486 7220

[www.MitsubishiElectric.com](http://www.MitsubishiElectric.com)

[www.mitsubishichips.eu](http://www.mitsubishichips.eu)